



4N135-P

Advance

Power MOSFET

4.0A, 1350V N-CHANNEL POWER MOSFET

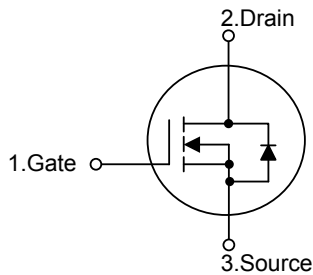
DESCRIPTION

The **UTC 4N135-P** is a high voltage and high current power MOSFET, designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and a high rugged avalanche characteristics. This power MOSFET is usually used at high speed switching applications in power supplies, PWM motor controls, high efficient AC to DC converters and bridge circuits.

FEATURES

- * $R_{DS(ON)} \leq 6.0 \Omega$ @ $V_{GS}=10V$, $I_D=2.0A$
- * High Switching Speed

SYMBOL



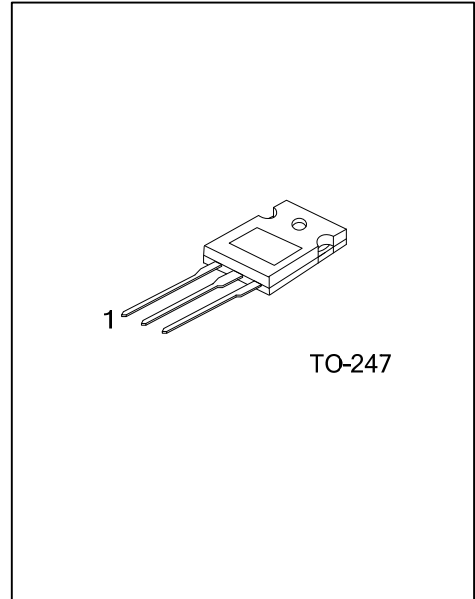
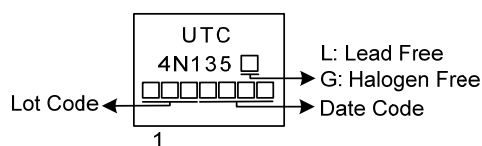
ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
4N135L-T47-T	4N135G-T47-T	TO-247	G	D	S	Tube

Note: Pin Assignment: G: Gate D: Drain S: Source

<p>4N135G-T47-T</p> <p>(1) Packing Type</p> <p>(2) Package Type</p> <p>(3) Green Package</p>	<p>(1) T: Tube</p> <p>(2) T47: TO-247</p> <p>(3) G: Halogen Free and Lead Free, L: Lead Free</p>
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MARKING



■ ABSOLUTE MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	1350	V
Gate-Source Voltage		V_{GSS}	± 30	V
Drain Current	Continuous	I_D	4	A
	Pulsed (Note 2)	I_{DM}	8	A
Power Dissipation		P_D	155	W
Junction Temperature		T_J	+150	$^\circ\text{C}$
Storage Temperature		T_{STG}	-55 ~ +150	$^\circ\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.
 2. Repetitive Rating: Pulse width limited by maximum junction temperature.

■ THERMAL DATA

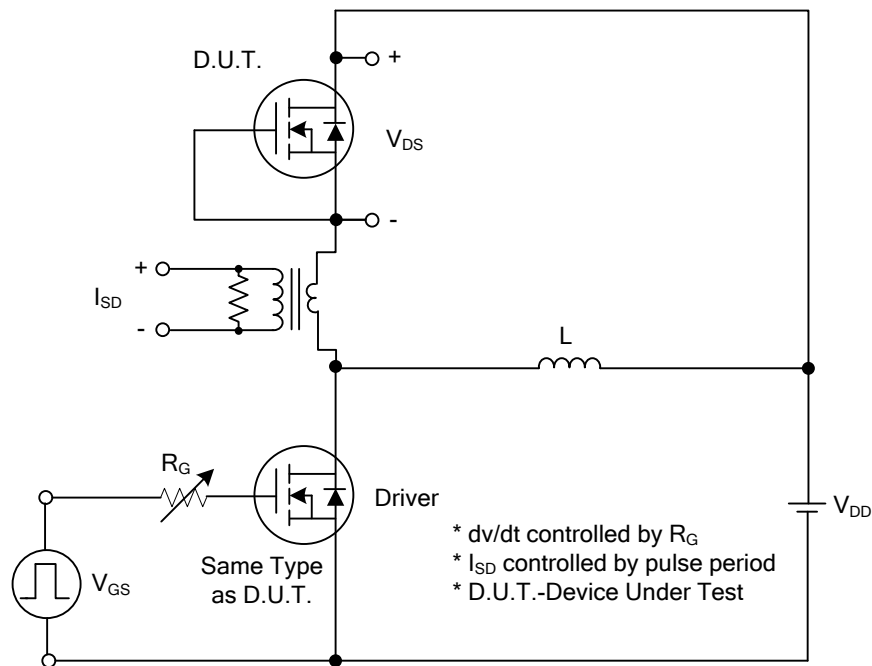
PARAMETER	SYMBOL	RATING	UNIT
Junction to Ambient	θ_{JA}	50	$^\circ\text{C/W}$
Junction to Case	θ_{JC}	0.8	$^\circ\text{C/W}$

■ ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$, unless otherwise specified)

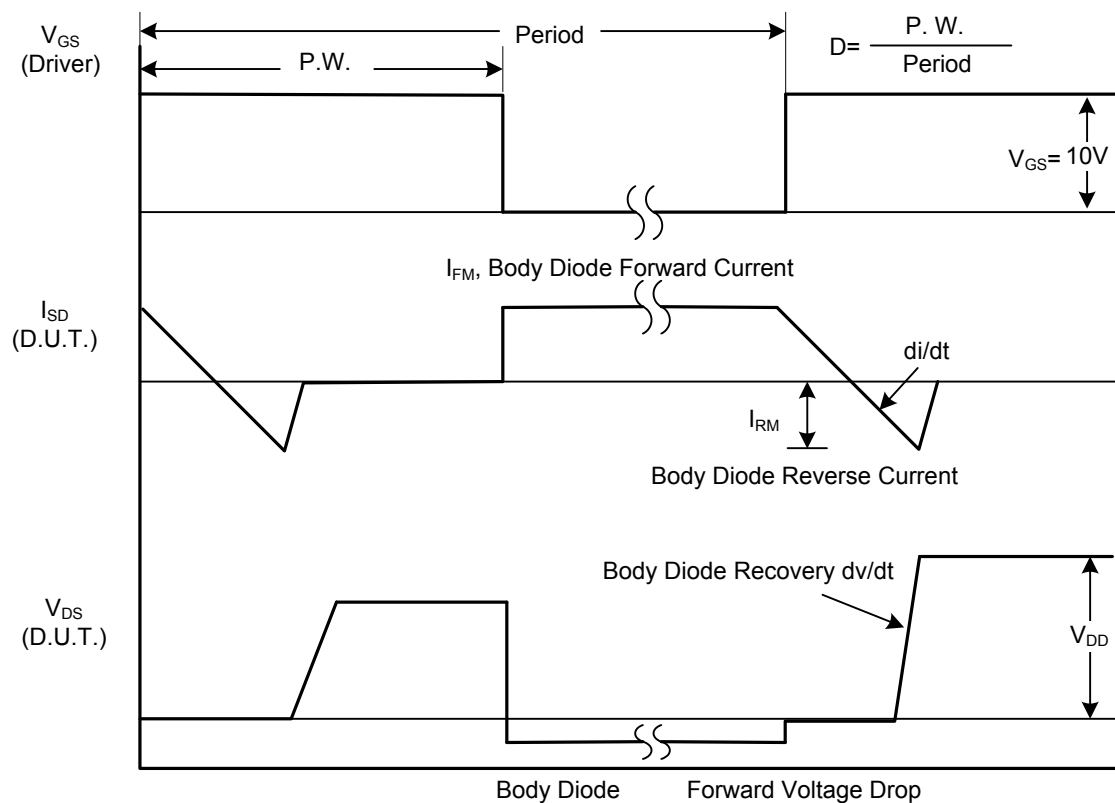
PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV _{DSS}	V _{GS} =0V, I _D = 250μA	1350			V
Drain-Source Leakage Current		I _{DSS}	V _{DS} =1350V, V _{GS} =0V			10	μA
Gate-Source Leakage Current	Forward	I _{GSS}	V _{GS} =30V, V _{DS} =0V			100	nA
	Reverse		V _{GS} =-30V, V _{DS} =0V			-100	nA
ON CHARACTERISTICS							
Gate Threshold Voltage		V _{GS(TH)}	V _{DS} =V _{GS} , I _D =250μA	3.0		5.0	V
Static Drain-Source On-State Resistance		R _{DS(ON)}	V _{GS} =10V, I _D =2.0A			6.0	Ω
DYNAMIC CHARACTERISTICS							
Input Capacitance		C _{ISS}	V _{GS} =0V, V _{DS} =25V, f=1.0 MHz		1210		pF
Output Capacitance		C _{OSS}			150		pF
Reverse Transfer Capacitance		C _{RSS}			79		pF
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS							
Maximum Body-Diode Continuous Current		I _S				4	A
Maximum Body-Diode Pulsed Current		I _{SM}				8	A
Drain-Source Diode Forward Voltage (Note 1)		V _{SD}	V _{GS} =0V, I _S =4.0A			1.4	V

Notes: 1. Pulse Test : Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$.
 2. Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS

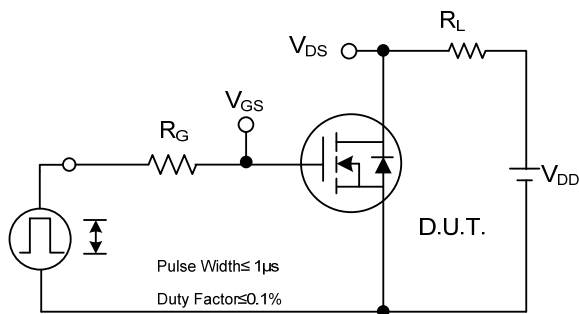


Peak Diode Recovery dv/dt Test Circuit

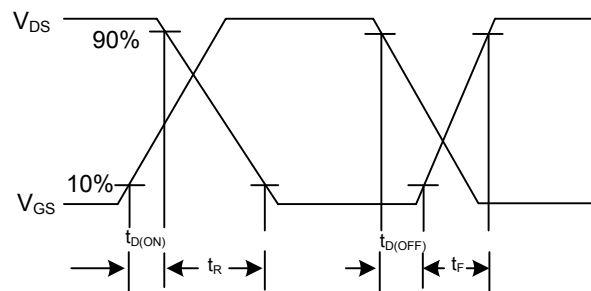


Peak Diode Recovery dv/dt Waveforms

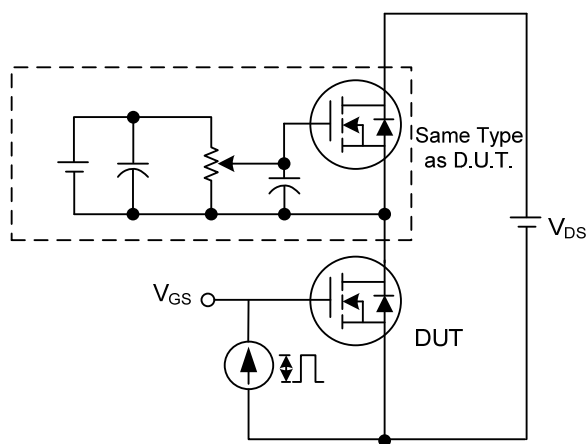
■ TEST CIRCUITS AND WAVEFORMS



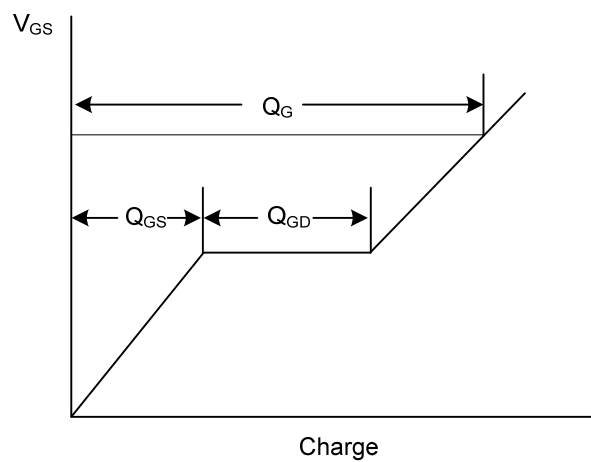
Switching Test Circuit



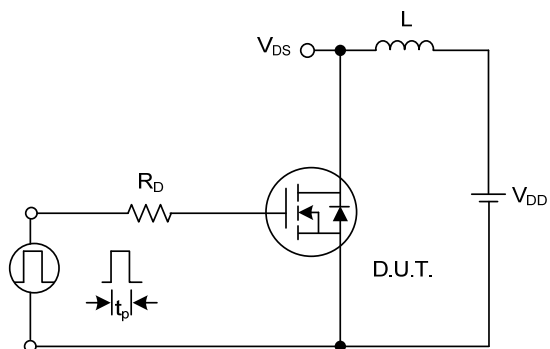
Switching Waveforms



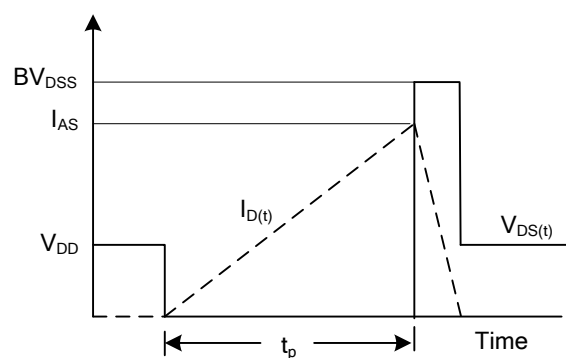
Gate Charge Test Circuit



Gate Charge Waveform



Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms

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